

N-channel TrenchMOS standard level FET Rev. 2 — 23 February 2011

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 185 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C		-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	<u>[1]</u>	-	-	75	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	167	W
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ T _j = 25 °C; see <u>Figure 9</u> ; see Figure 10		-	10.2	12	mΩ



Max

173

Unit

mJ

N-channel TrenchMOS standard level FET

Table 1. Quick reference data ... continued Conditions Symbol Parameter Min Тур Avalanche ruggedness $I_{\rm D} = 75 \; {\rm A}; \; {\rm V}_{\rm sup} \le 55 \; {\rm V}; \\ {\rm R}_{\rm GS} = 50 \; \Omega; \; {\rm V}_{\rm GS} = 10 \; {\rm V};$ E_{DS(AL)S} non-repetitive _ _ drain-source $T_{i(init)} = 25$ °C; unclamped avalanche energy

		·)(IIIII) = • • ; •···••••••				
Dynamic o	characteristics					
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 44 V; T _j = 25 °C; see <u>Figure 11</u>	-	12	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2. **Pinning information** Pin Simplified outline **Graphic symbol** Symbol Description gate 1 G mb D 2 drain^[1] D 3 S source mb D mounting base; connected to drain mbb076 2 SOT428 (DPAK)

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK7212-55B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

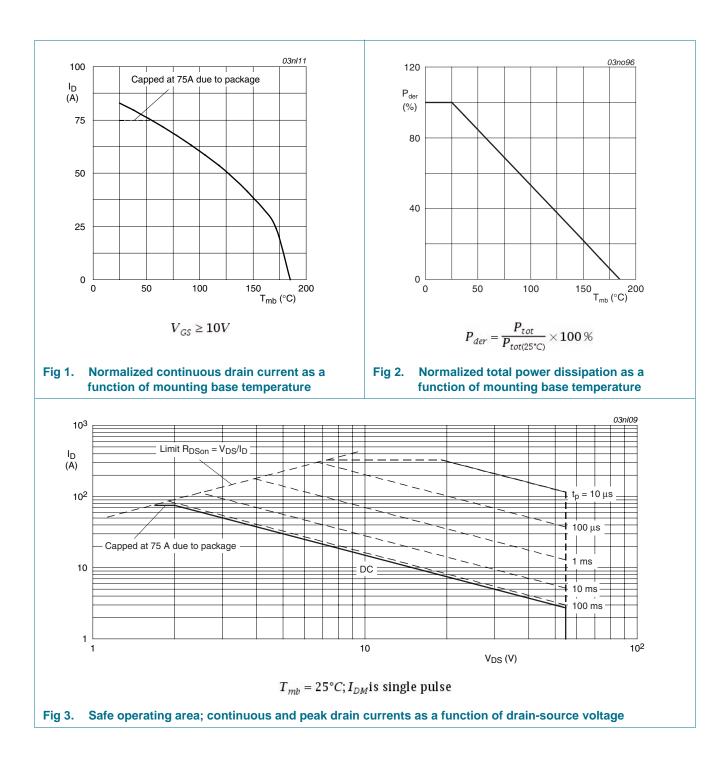
Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C	-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	<u>[1]</u> _	83	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u> _	59	А
		$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 3}}{\text{Figure 1}};$	[2] _	75	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>	-	335	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	167	W
T _{stg}	storage temperature		-55	185	°C
Tj	junction temperature		-55	185	°C
Source-drai	in diode				
ls	source current	T _{mb} = 25 °C	[2]	75	А
			<u>[1]</u> _	83	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	335	А
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 75 A; V _{sup} ≤ 55 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped	-	173	mJ

[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.

BUK7212-55B

N-channel TrenchMOS standard level FET



5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71.4	-	K/W

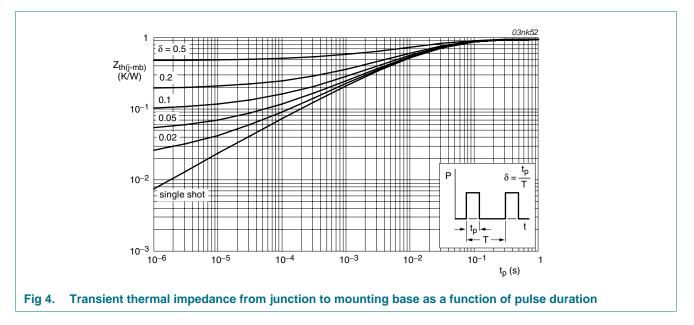


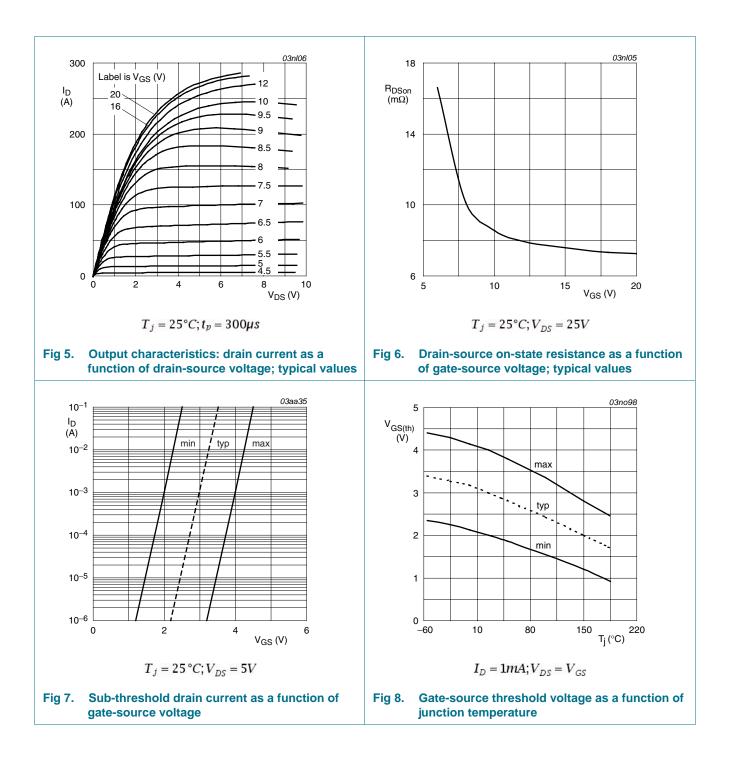
Table 5. Thermal characteristics

6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
(DR)D00	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 8</u>	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 185 °C; see <u>Figure 8</u>	0.9	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 8</u>	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 185 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 185 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	-	25	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	10.2	12	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	35	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 11</u>	-	9	-	nC
Q_{GD}	gate-drain charge		-	12	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1840	2453	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 12$	-	379	455	pF
C _{rss}	reverse transfer capacitance		-	165	226	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	18	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	91	-	ns
t _{d(off)}	turn-off delay time		-	48	-	ns
t _f	fall time		-	45	-	ns
L _D	internal drain inductance	measured from drain to center of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad; $T_j = 25 \text{ °C}$	-	75	-	nH
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 18 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 13</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/µs;	-	67	-	ns
Qr	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C	-	65	-	nC

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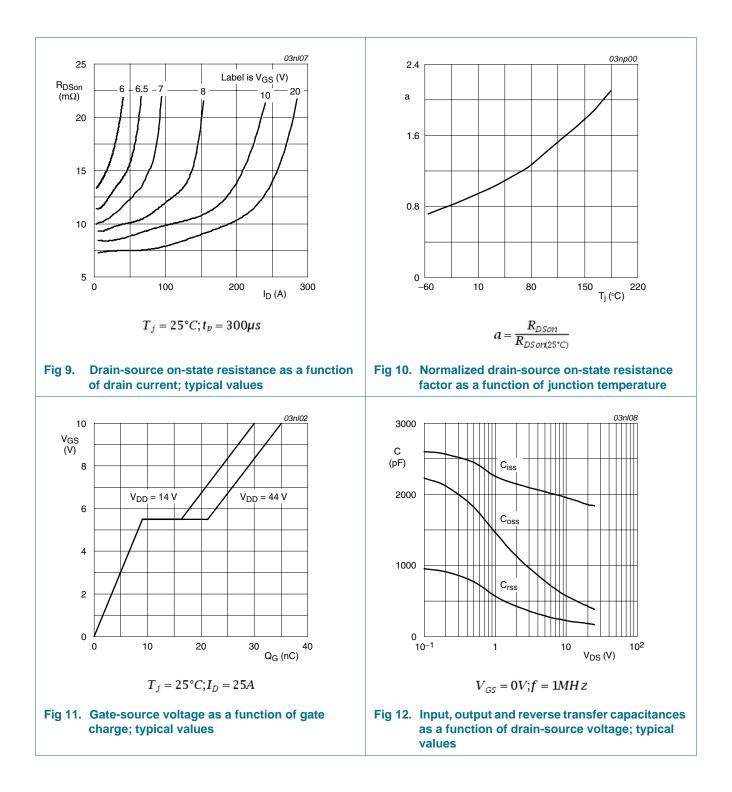
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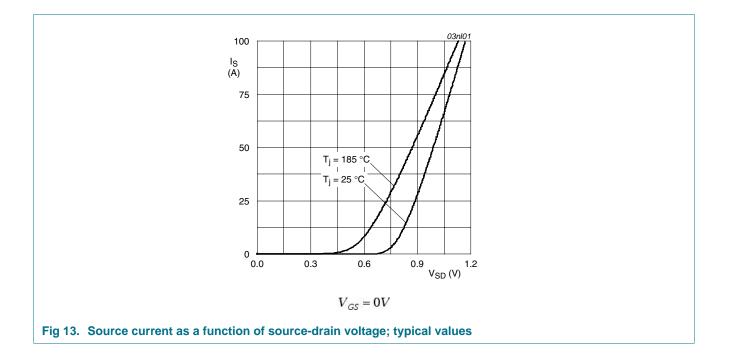
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7. Package outline

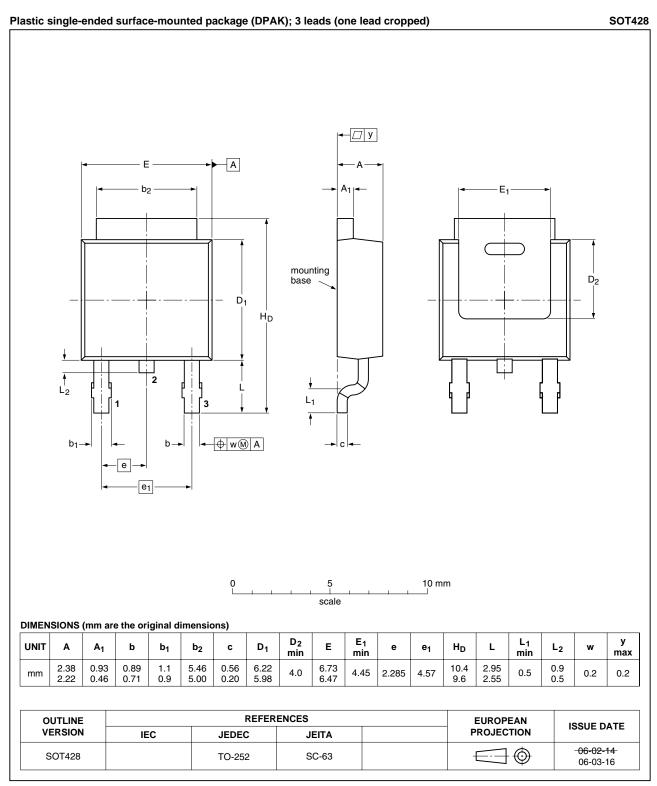


Fig 14. Package outline SOT428 (DPAK)

BUK7212-55B Product data sheet

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8. Revision history

Table 7. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7212-55B v.2	20110223	Product data sheet	-	BUK7212_55B-01
Modifications:	of NXP Semic	this data sheet has been rec conductors. ve been adapted to the new		
BUK7212 55B-01	20040123	Product data	company name where	appropriato.
(9397 750 12229)	20040123	FIDUUCIUAIA	-	-

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9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BUK7212-55B

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N-channel TrenchMOS standard level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values
5	Thermal characteristics5
6	Characteristics6
7	Package outline10
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks
10	Contact information13

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